

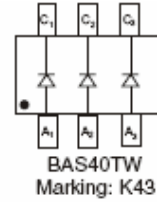
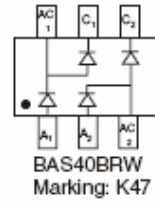
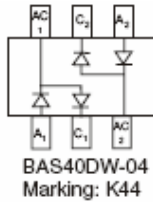
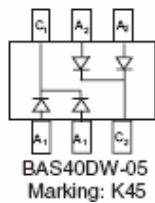
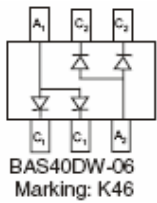
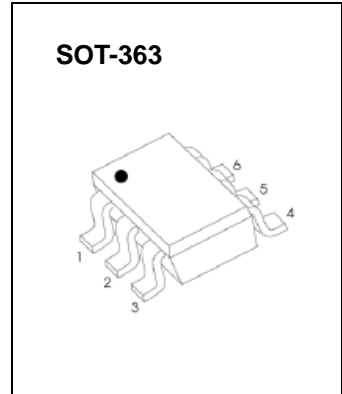


Plastic-Encapsulate Transistors

SCHOTTKY BARRIER DIODE ARRAYS

FEATURES

- Low Forward voltage drop
- Fast switching



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage DC Blocking Voltage	V_{RM} V_R	40	V
Average Rectified Output Current	I_O	200	mA
Power Dissipation	P_d	200	mW
Thermal Resistance. Junction to Ambient Air	$R_{\theta JA}$	625	°C/W
Junction temperature	T_J	125	°C
Storage temperature range	T_{STG}	-65-125	°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=10\mu A$	40		V
Reverse voltage leakage current	I_R	$V_R=30V$		200	nA
Forward voltage	V_F	$I_F=1mA$ $I_F=40mA$		380 1000	mV
Total capacitance	C_T	$V_R=0, f=1MHz$		5	pF
Reverse recovery time	t_{rr}	$I_F=10mA, I_R=I_F=1mA$ $R_L=100\Omega$		5	ns



Typical Characteristics

